

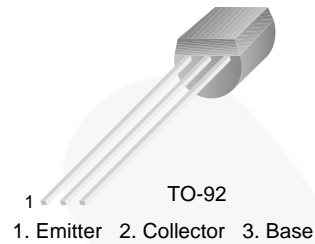


KSC1815

NPN Epitaxial Silicon Transistor

Features

- Audio Frequency Amplifier and High-Frequency OSC
- Complement to KSA1015
- Collector-Base Voltage: $V_{CBO} = 50\text{ V}$



Ordering Information

Part Number	Top Mark	Package	Packing Method
KSC1815YTA	YC&3	TO-92 3L	Ammo

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	50	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	150	mA
I_B	Base Current	50	mA
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Characteristics⁽¹⁾

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Max.	Unit
P_D	Total Device Dissipation	400	mW
	Derate Above 25°C	3.2	mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	312	$^\circ\text{C}/\text{W}$

Note:

1. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

Electrical Characteristics

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{CBO}	Collector-Base Voltage	$I_C = 1 \text{ mA}, I_E = 0$	60			V
BV_{CEO}	Collector-Emitter Voltage	$I_C = 10 \text{ mA}, I_B = 0$	50			V
BV_{EBO}	Emitter-Base Voltage	$I_E = 10 \mu\text{A}, I_C = 0$	5			V
I_{CBO}	Collector Cut-Off Current	$V_{CB} = 60 \text{ V}, I_E = 0$			0.1	μA
I_{EBO}	Emitter Cut-Off Current	$V_{EB} = 5 \text{ V}, I_C = 0$			0.1	μA
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$		0.10	0.25	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$			1.0	V
h_{FE1}	DC Current Gain	$V_{CE} = 6 \text{ V}, I_C = 2 \text{ mA}$	70		700	
h_{FE2}	DC Current Gain	$V_{CE} = 6 \text{ V}, I_C = 150 \text{ mA}$	25			
f_T	Current Gain Bandwidth Product	$V_{CE} = 10 \text{ V}, I_C = 1 \text{ mA}$	80			MHz
C_{ob}	Output Capacitance	$V_{CB} = 10 \text{ V}, I_E = 0,$ $f = 1 \text{ MHz}$		2.0	3.0	pF
N_F	Noise Figure	$V_{CE} = 6 \text{ V}, I_C = 0.1 \text{ mA},$ $R_S = 10 \text{ k}\Omega, f = 1 \text{ Hz}$		1.0	10.0	dB

 h_{FE} Classification

Classification	O	Y	GR	L
h_{FE1}	70 ~ 140	120 ~ 240	200 ~ 400	350 ~ 700

Typical Performance Characteristics

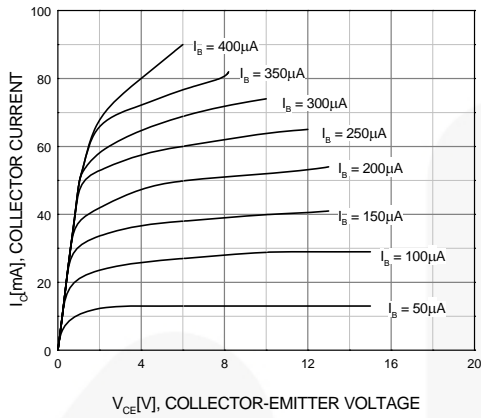


Figure 1. Static Characteristic

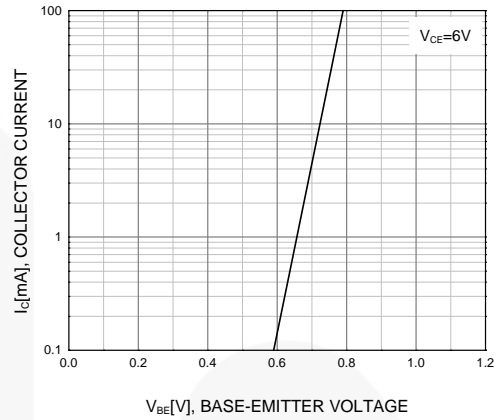


Figure 2. Transfer Characteristic

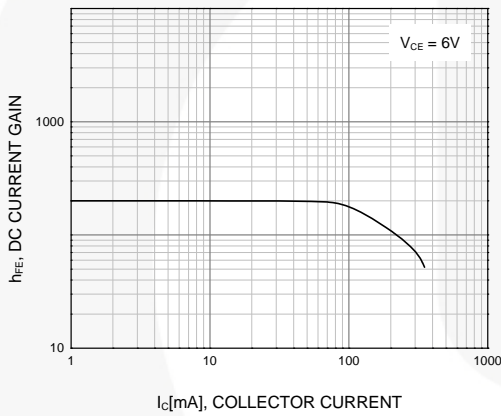


Figure 3. DC Current Gain

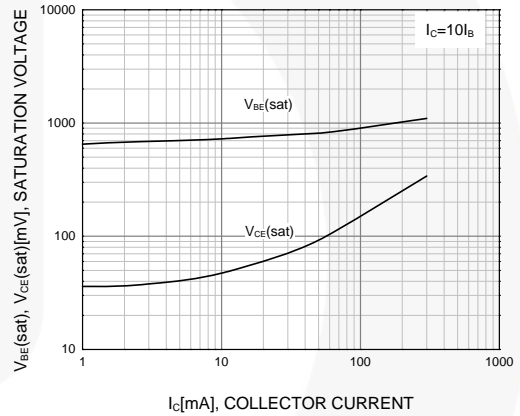


Figure 4. Base-Emitter Saturation Voltage and Collector-Emitter Saturation Voltage

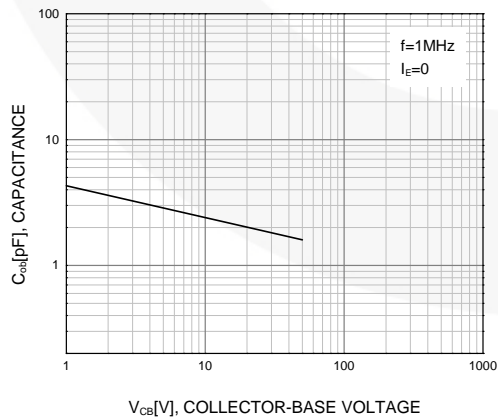


Figure 5. Output Capacitance

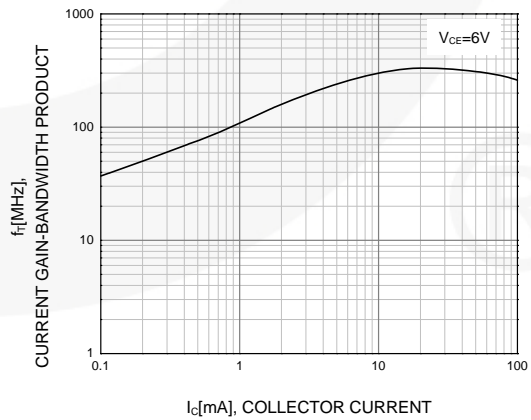
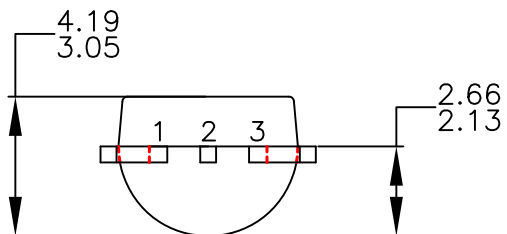
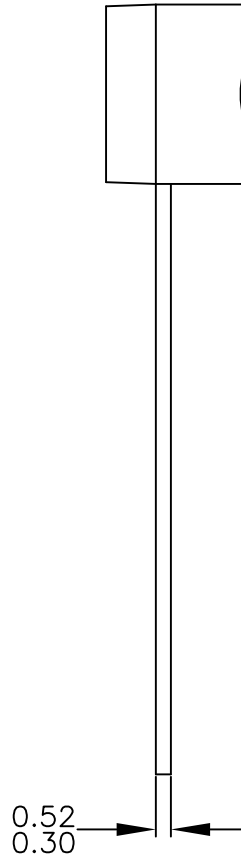
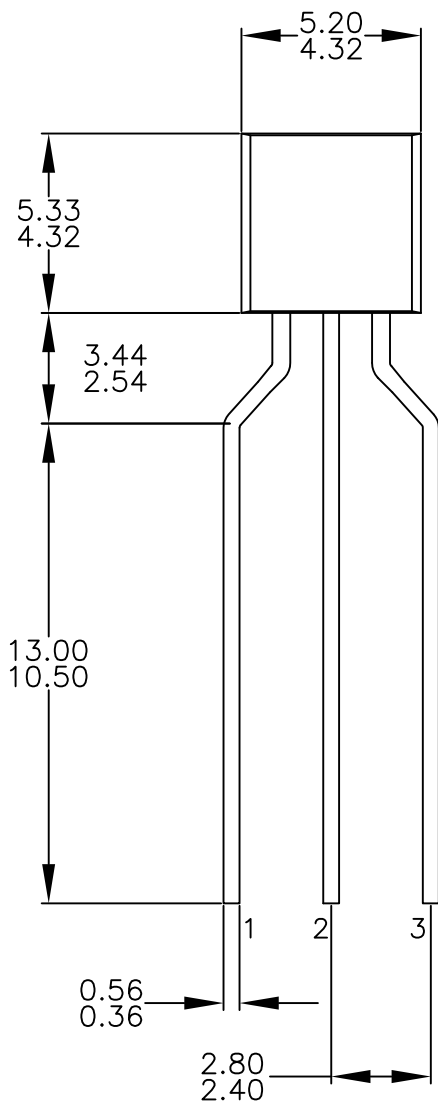


Figure 6. Current Gain Bandwidth Product



NOTES: UNLESS OTHERWISE SPECIFIED

- A. DRAWING CONFORMS TO JEDEC MS-013, VARIATION AC.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5M-2009.
- D. DRAWING FILENAME: MKT-ZA03FREV3.
- E. FAIRCHILD SEMICONDUCTOR.